



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- Epitaxial Planar Die Construction
- Nominal 47k Ω Built-In Biasing Resistor

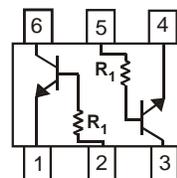
Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 Ⓢ
- Weight: 0.015 grams (Approximate)

SOT563



Top View



Device Schematic

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage	V_{CC}	50	V
Input Voltage	V_{IN}	-10 to +40	V
Output Current	$I_{C(MAX)}$	100	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Notes 5 & 6)	P_D	150	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	—	—	V	$I_C = 50\mu\text{A}$
Collector-Emitter Breakdown Voltage	BV_{CEO}	50	—	—	V	$I_C = 1\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	5	—	—	V	$I_E = 50\mu\text{A}$
Collector Cutoff Current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 50\text{V}$
Emitter Cutoff Current	I_{EBO}	—	—	0.5	μA	$V_{EB} = 4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C/I_B = 1\text{mA} / 0.1\text{mA}$
DC Current Transfer Ratio	h_{FE}	100	250	600	—	$I_C = 1\text{mA}, V_{CE} = 5\text{V}$
Input Resistor (R1)	R_1	32.9	47 Ω	61.1	k Ω	—
Gain-Bandwidth Product (Note 7)	f_T	—	250	—	MHz	$V_{CE} = 10\text{V}, I_E = -5\text{mA}, f = 100\text{MHz}$

Notes: 5. Mounted on FR4 PC Board with minimum recommended pad layout.
 6. 200mW per element must not be exceeded.
 7. Transistor - For Reference Only

Typical Curves (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

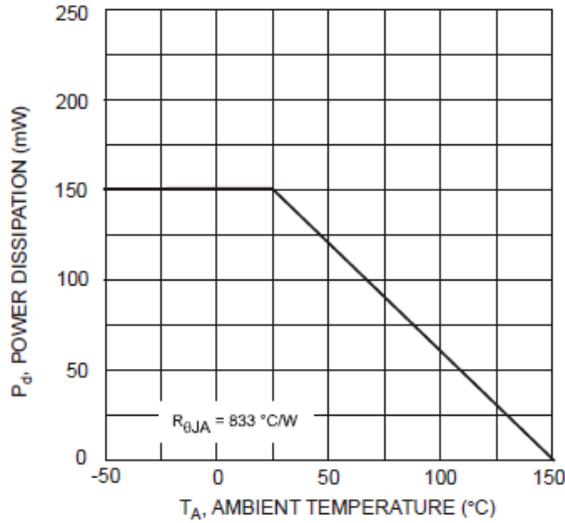


Fig. 1 Derating Curve

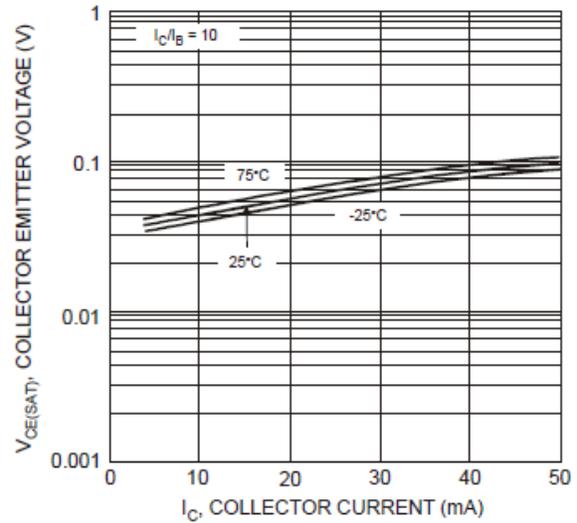


Fig. 2 $V_{CE(SAT)}$ vs. I_C

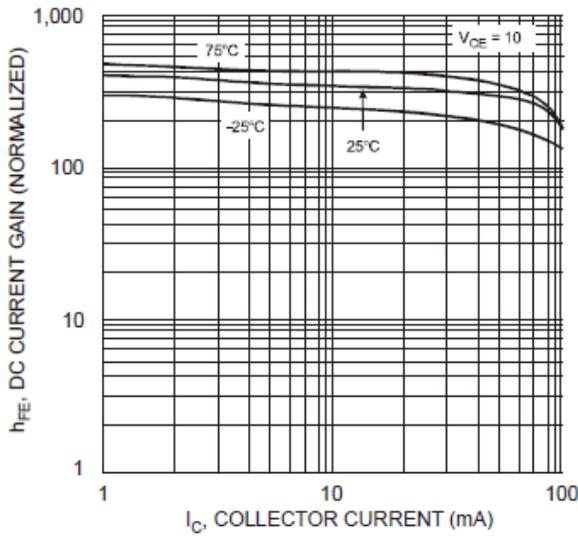


Fig. 3 DC Current Gain

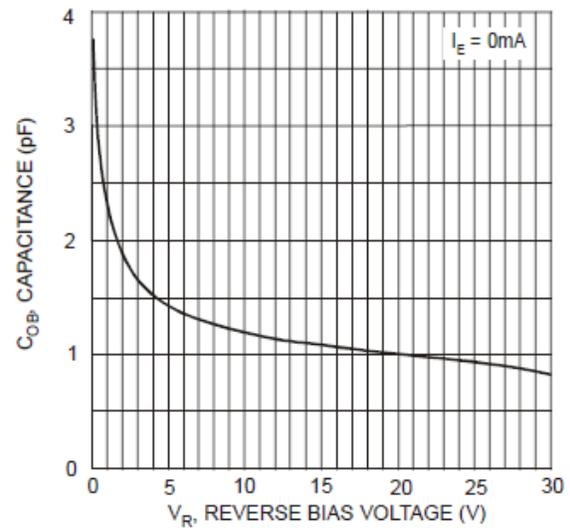


Fig. 4 Output Capacitance

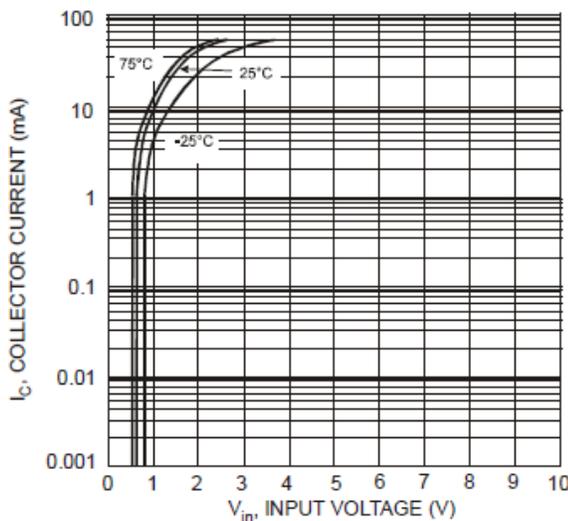


Fig. 5 Collector Current vs. Input Voltage

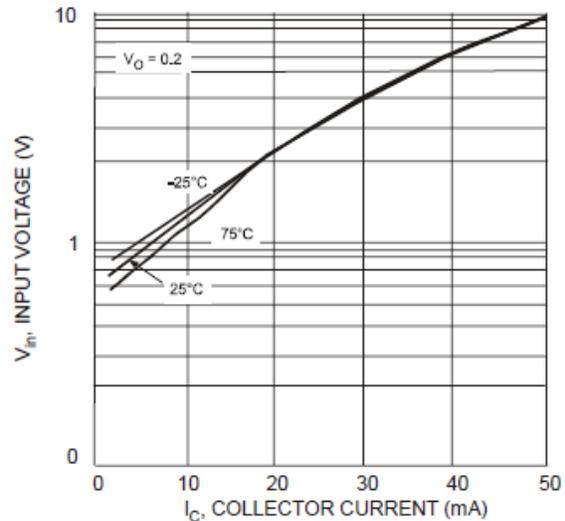
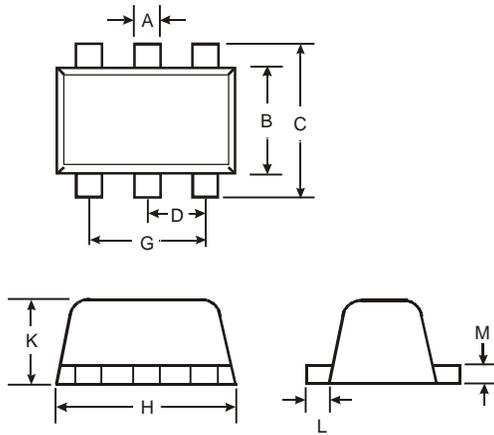


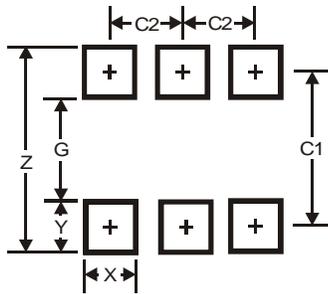
Fig. 6 Input Voltage vs. Collector Current

Package Outline Dimensions



SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5